



STK11C68-M

CMOS nvSRAM

High Performance

8K x 8 Nonvolatile Static RAM

MIL-STD-883/SMD # 5962-92324

FEATURES

- 30, 35, 45 and 55ns Access Times
- 15, 20 and 25ns Output Enable Access
- Unlimited Read and Write to SRAM
- Software *STORE* Initiation
- Automatic *STORE* Timing
- 10^4 or 10^5 *STORE* cycles to EEPROM
- 10 year data retention in EEPROM
- Automatic *RECALL* on Power Up
- Software *RECALL* Initiation
- Unlimited *RECALL* cycles from EEPROM
- Single $5V \pm 10\%$ Operation
- Available in multiple standard packages

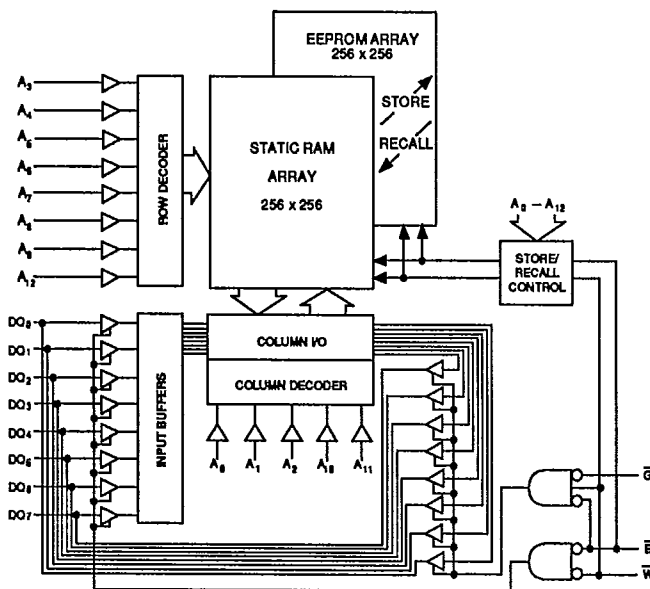
DESCRIPTION

The Simtek STK11C68-M is a fast static RAM (30, 35, 45 and 55ns), with a nonvolatile electrically-erasable PROM (EEPROM) element incorporated in each static memory cell. The SRAM can be read and written an unlimited number of times, while independent non-volatile data resides in EEPROM. Data transfers from the SRAM to the EEPROM (*STORE*), or from the EEPROM to the SRAM (*RECALL*) are initiated through software sequences. It combines the high performance and ease of use of a fast SRAM with nonvolatile data integrity.

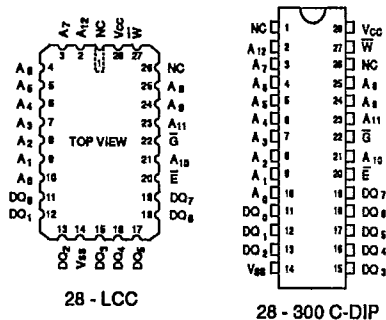
The STK11C68-M is pin compatible with industry standard SRAMs and is available in a 28-pin 300 mil ceramic DIP or 28-pad LCC package. Commercial and industrial devices are also available.

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LOGIC BLOCK DIAGRAM



PIN CONFIGURATIONS



PIN NAMES

Pin Name	Description
$A_0 - A_{12}$	Address Inputs
\bar{W}	Write Enable
$DQ_0 - DQ_7$	Data In/Out
\bar{E}	Chip Enable
\bar{O}	Output Enable
V_{CC}	Power (+5V)
V_{SS}	Ground

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ABSOLUTE MAXIMUM RATINGS^a

Voltage on typical input relative to V_{SS}	-0.6V to 7.0V
Voltage on DQ_{0-7} and \bar{G}	-0.5V to ($V_{CC}+0.5V$)
Temperature under bias.....	-55°C to 125°C
Storage temperature.....	-65°C to 150°C
Power dissipation.....	1W
DC output current.....	.15mA

(One output at a time, one second duration)

Note a: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

DC CHARACTERISTICS

 $(V_{CC} = 5.0V \pm 10\%)$

SYMBOL	PARAMETER	MIN	MAX	UNITS	NOTES
I_{CC1}^b	Average V_{CC} Current		85	mA	$t_{AVAV} = 30ns$
			80	mA	$t_{AVAV} = 35ns$
			75	mA	$t_{AVAV} = 45ns$
			70	mA	$t_{AVAV} = 55ns$
I_{CC2}^d	Average V_{CC} Current during STORE cycle		50	mA	$E \geq (V_{CC} - 0.2V)$ all others $V_{IN} \leq 0.2V$ or $\geq (V_{CC} - 0.2V)$
I_{SB1}^c	Average V_{CC} Current (Standby, Cycling TTL Input Levels)		30	mA	$t_{AVAV} = 30ns$
			27	mA	$t_{AVAV} = 35ns$
			23	mA	$t_{AVAV} = 45ns$
			20	mA	$t_{AVAV} = 55ns$
					$\bar{E} \geq V_{IH}$; all others cycling
I_{SB2}^c	Average V_{CC} Current (Standby, Stable CMOS Input Levels)		2	mA	$E \geq (V_{CC} - 0.2V)$ all others $V_{IN} \leq 0.2V$ or $\geq (V_{CC} - 0.2V)$
I_{ILK}	Input Leakage Current (Any Input)		± 1	μA	$V_{CC} = \max$ $V_{IN} = V_{SS}$ to V_{CC}
I_{OLK}	Off State Output Leakage Current		± 5	μA	$V_{CC} = \max$ $V_{IN} = V_{SS}$ to V_{CC}
V_{IH}	Input Logic "1" Voltage	2.2	$V_{CC} + .5$	V	All Inputs
V_{IL}	Input Logic "0" Voltage	$V_{SS} - .5$	0.8	V	All Inputs
V_{OH}	Output Logic "1" Voltage	2.4		V	$I_{OUT} = -4mA$
V_{OL}	Output Logic "0" Voltage		0.4	V	$I_{OUT} = 8mA$
T_A	Operating Temperature	-55	125	°C	

Note b: I_{CC1} is dependent on output loading and cycle rate. The specified values are obtained with outputs unloaded.

Note c: Bringing $\bar{E} \geq V_{IH}$ will not produce standby current levels until any nonvolatile cycle in progress has timed out. See MODE SELECTION table.

Note d: I_{CC2} is the average current required for the duration of the store cycle (t_{STORE}) after the sequence (t_{WC}) that initiates the cycle.

AC TEST CONDITIONS

Input Pulse Levels.....	V_{SS} to 3V
Input Rise and Fall Times.....	$\leq 5ns$
Input and Output Timing Reference Levels.....	1.5V
Output Load.....	See Figure 1

CAPACITANCE ($T_A=25^\circ C, f=1.0MHz$)^e

SYMBOL	PARAMETER	MAX	UNITS	CONDITIONS
C_{IN}	Input Capacitance	5	pF	$\Delta V = 0$ to 3V
C_{OUT}	Output Capacitance	7	pF	$\Delta V = 0$ to 3V

Note e: These parameters are guaranteed but not tested.

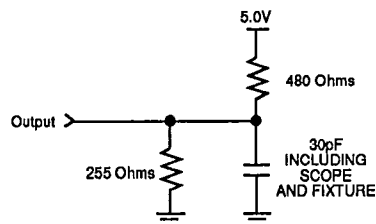


Figure 1: AC Output Loading

READ CYCLES #1 & #2

 $(V_{CC} = 5.0V \pm 10\%)$

NO.	SYMBOLS		PARAMETER	STK11C68-30M		STK11C68-35M		STK11C68-45M		STK11C68-55M		UNITS
	#1, #2	AHL		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
1	t_{ELOV}^g	t_{ACS}	Chip Enable Access Time		30		35		45		55	ns
2	t_{AVAVR}^g	t_{RC}	Read Cycle Time	30		35		45		55		ns
3	t_{AVQV}^h	t_{AA}	Address Access Time		30		35		45		55	ns
4	t_{GLOV}	t_{OE}	Output Enable to Data Valid		15		20		25		25	ns
5	t_{AXOX}	t_{OH}	Output Hold After Address Change	5		5		5		5		ns
6	t_{ELOX}	t_{LZ}	Chip Enable to Output Active	5		5		5		5		ns
7	t_{EHOZ}^i	t_{HZ}	Chip Disable to Output Inactive		15		17		20		25	ns
8	t_{GLOX}	t_{OLZ}	Output Enable to Output Active	0		0		0		0		ns
9	t_{GHOZ}^i	t_{OHZ}	Output Disable to Output Inactive		15		17		20		25	ns
10	t_{ELCCH}^e	t_{PA}	Chip Enable to Power Active	0		0		0		0		ns
11	$t_{EHICCL}^{e,g}$	t_{PS}	Chip Disable to Power Standby		25		25		25		25	ns
11A	t_{WHQV}	t_{WR}	Write Recovery Time		35		45		55		65	ns

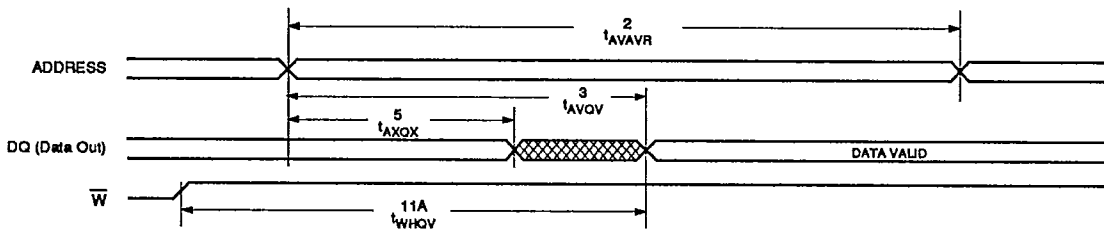
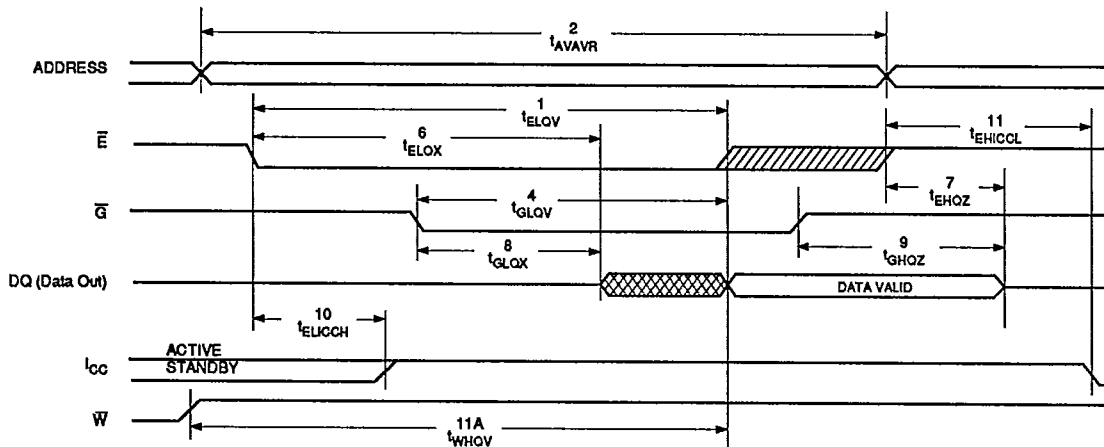
Note c: Bringing \bar{E} high will not produce standby currents until any nonvolatile cycle in progress has timed out. See MODE SELECTION table.

Note e: Parameter guaranteed but not tested.

Note g: For READ CYCLE #1 and #2, \bar{W} must be high for entire cycle.

Note h: Device is continuously selected with \bar{E} low and \bar{G} low.

Note i: Measured $\pm 200mV$ from steady state output voltage.

READ CYCLE #1 ^{g,h}READ CYCLE #2 ^g

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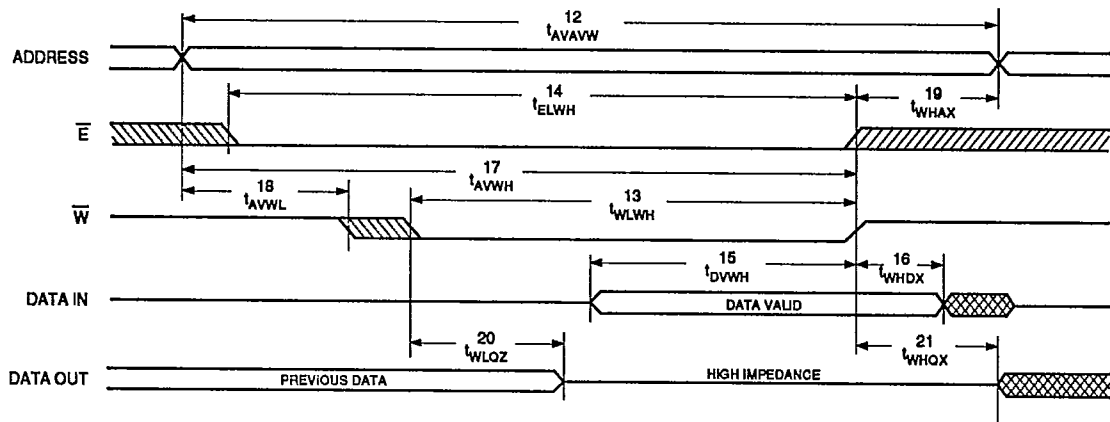
WRITE CYCLES #1 & #2; \bar{G} high (this table is effective 3/31/94) $(V_{CC} = 5.0V \pm 10\%)$

NO.	SYMBOLS			PARAMETER	STK11C68-30M		STK11C68-35M		STK11C68-45M		STK11C68-55M		UNITS
	#1	#2	Ail.		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
12	t_{AVAW}	t_{AVAW}	t_{WC}	Write Cycle Time	30		35		45		55		ns
13	t_{WLWH}	t_{WLEH}	t_{WP}	Write Pulse Width	25		30		35		45		ns
14	t_{ELWH}	t_{ELEH}	t_{CW}	Chip Enable to End of Write	25		30		35		45		ns
15	t_{DVWH}	t_{DVEH}	t_{DW}	Data Set-up to End of Write	15		18		20		30		ns
16	t_{WHDX}	t_{EHDX}	t_{DH}	Data Hold After End of Write	0		0		0		0		ns
17	t_{AVWH}	t_{AVEH}	t_{AW}	Address Set-up to End of Write	25		30		35		45		ns
18	t_{AVWL}	t_{AVEL}	t_{AS}	Address Set-up to Start of Write	0		0		0		0		ns
19	t_{WHAX}	t_{EHAX}	t_{WR}	Address Hold After End of Write	0		0		0		0		ns

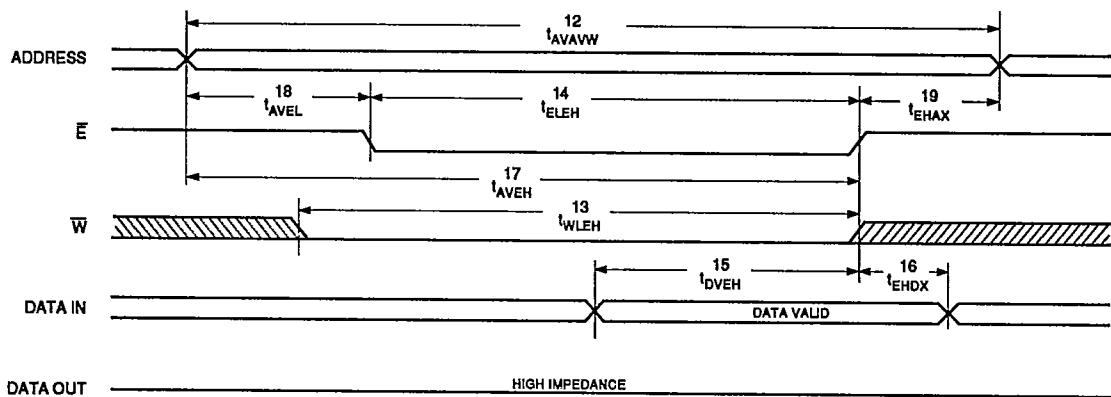
WRITE CYCLES #1 & #2; \bar{G} low

NO.	SYMBOLS			PARAMETER	STK11C68-30M		STK11C68-35M		STK11C68-45M		STK11C68-55M		UNITS
	#1	#2	Ail.		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
12	t_{AVAW}	t_{AVAW}	t_{WC}	Write Cycle Time	45		45		45		55		ns
13	t_{WLWH}	t_{WLEH}	t_{WP}	Write Pulse Width	35		35		35		45		ns
14	t_{ELWH}	t_{ELEH}	t_{CW}	Chip Enable to End of Write	35		35		35		45		ns
15	t_{DVWH}	t_{DVEH}	t_{DW}	Data Set-up to End of Write	30		30		30		30		ns
16	t_{WHDX}	t_{EHDX}	t_{DH}	Data Hold After End of Write	0		0		0		0		ns
17	t_{AVWH}	t_{AVEH}	t_{AW}	Address Set-up to End of Write	35		35		35		45		ns
18	t_{AVWL}	t_{AVEL}	t_{AS}	Address Set-up to Start of Write	0		0		0		0		ns
19	t_{WHAX}	t_{EHAX}	t_{WR}	Address Hold After End of Write	0		0		0		0		ns
20	t_{WLOZ}^m		t_{WZ}	Write Enable to Output Disable		35		35		35		35	ns
21	t_{WHOX}		t_{OW}	Output Active After End of Write	5		5		5		5		ns

Note l: Measured $\pm 200mV$ from steady state output voltage.Note k: \bar{E} or \bar{W} must be $\geq V_{IH}$ during address transitions.Note m: If \bar{W} is low when \bar{E} goes low, the outputs remain in the high impedance state.

WRITE CYCLE #1: \overline{W} CONTROLLED^k

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WRITE CYCLE #2: \overline{E} CONTROLLED^k

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NONVOLATILE MEMORY OPERATION

MODE SELECTION

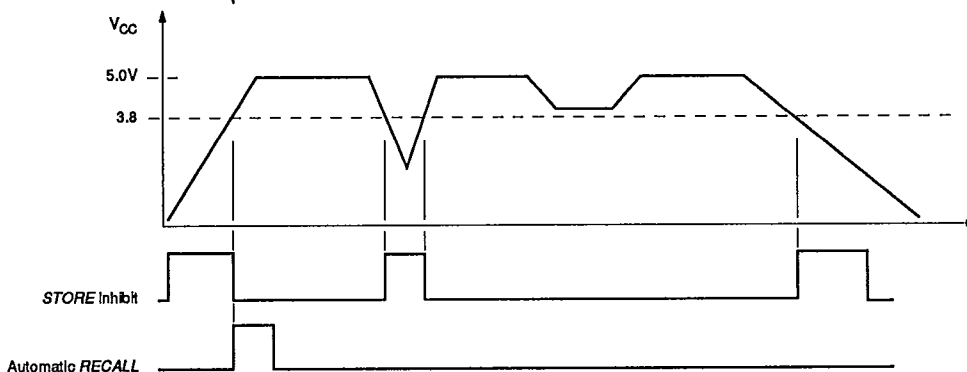
\bar{E}	\bar{W}	$A_{12} - A_0(\text{hex})$	MODE	I/O	POWER	NOTES
H	X	X	Not Selected	Output High Z	Standby	
L	H	X	Read SRAM	Output Data	Active	o
L	L	X	Write SRAM	Input Data	Active	
L	H	0000	Read SRAM	Output Data	Active	n,o
		1555	Read SRAM	Output Data		n,o
		0AAA	Read SRAM	Output Data		n,o
		1FFF	Read SRAM	Output Data		n,o
		10F0	Read SRAM	Output Data		n,o
		0F0F	Nonvolatile STORE	Output High Z		I_{CC2}
L	H	0000	Read SRAM	Output Data	Active	n,o
		1555	Read SRAM	Output Data		n,o
		0AAA	Read SRAM	Output Data		n,o
		1FFF	Read SRAM	Output Data		n,o
		10F0	Read SRAM	Output Data		n,o
		0F0E	Nonvolatile RECALL	Output High Z		

Note n: The six consecutive addresses must be in order listed - (0000, 1555, 0AAA, 1FFF, 10F0, 0F0F) for a *STORE* cycle or (0000, 1555, 0AAA, 1FFF, 10F0, 0F0E) for a *RECALL* cycle. \bar{W} must be high during all six consecutive cycles. See *STORE* cycle and *RECALL* cycle tables and diagrams for further details.

Note o: I/O state assumes that $\bar{Q} \leq V_{IL}$. Initiation and operation of nonvolatile cycles does not depend on the state of \bar{Q} .

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STORE CYCLE INHIBIT and AUTOMATIC POWER-UP RECALL



STORE/RECALL CYCLE

 $(V_{CC} = 5.0V \pm 10\%)$

NO.	SYMBOLS		PARAMETER	STK11C68-30M		STK11C68-35M		STK11C68-45M		STK11C68-55M		UNITS
	#1	Alt.		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
22	t_{AVAVN}	t_{RC}	STORE/RECALL Initiation Cycle Time	30		35		45		55		ns
23	t_{ELOZ}^p		Chip Enable to Output Inactive		75		75		75		85	ns
24	t_{ELOXS}	t_{STORE}^q	STORE Cycle Time		12		12		12		12	ms
25	t_{ELOXR}	t_{RECALL}^r	RECALL Cycle Time		25		25		25		25	μs
26	t_{AVELN}^s	t_{AE}	Address Set-up to Chip Enable	0		0		0		0		ns
27	$t_{ELEHN}^{s,1}$	t_{EP}	Chip Enable Pulse Width	20		25		35		45		ns
28	t_{EHAXN}^s	t_{EA}	Chip Disable to Address Change	0		0		0		0		ns

Note p: Once the software STORE or RECALL cycle is initiated, it completes automatically, ignoring all inputs.

Note q: Note that STORE cycles (but not RECALLs) are aborted by $V_{CC} < 3.8V$ (STORE inhibit).

Note r: A RECALL cycle is initiated automatically at power up when V_{CC} exceeds 3.8V. t_{RECALL} is measured from the point at which V_{CC} exceeds 4.5V.

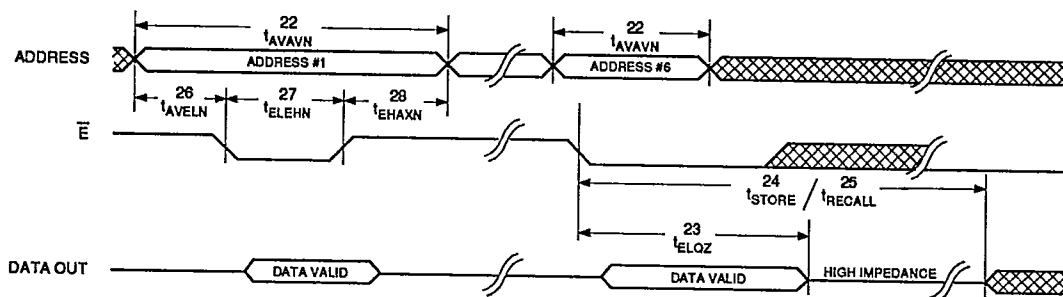
Note s: Noise on the \bar{E} pin may trigger multiple read cycles from the same address and abort the address sequence.

Note t: If the Chip Enable Pulse Width is less than t_{ELOV} (see READ CYCLE #2) but greater than or equal to t_{ELEHN} , then the data may not be valid at the end of the low pulse, however the STORE or RECALL will still be initiated.

Note u: \bar{W} must be HIGH when \bar{E} is LOW during the address sequence in order to initiate a nonvolatile cycle. \bar{G} may be either HIGH or LOW throughout.

Addresses #1 through #6 are found in the MODE SELECTION table. Address #6 determines whether the STK11C68-M performs a STORE or RECALL.

Note v: \bar{E} must be used to clock in the address sequence for the Software STORE and RECALL cycles.

STORE/RECALL CYCLE ^{u,v}

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DEVICE OPERATION

The STK11C68-M has two separate modes of operation: SRAM mode and nonvolatile mode. In SRAM mode, the memory operates as an ordinary static RAM. In nonvolatile operation, data is transferred from SRAM to EEPROM or from EEPROM to SRAM. In this mode SRAM functions are disabled.

SRAM READ

The STK11C68-M performs a READ cycle whenever \bar{E} and \bar{G} are LOW while \bar{W} is HIGH. The address specified on pins A_{0-12} determines which of the 8192 data bytes will be accessed. When the READ is initiated by an address transition, the outputs will be valid after a delay of t_{AVQV} (READ CYCLE #1). If the READ is initiated by \bar{E} or \bar{G} , the outputs will be valid at t_{ELQV} or at t_{GLQV} , whichever is later (READ CYCLE #2). The data outputs will repeatedly respond to address changes within the t_{AVQV} access time without the need for transitions on any control input pins, and will remain valid until another address change or until \bar{E} or \bar{G} is brought HIGH or \bar{W} is brought LOW.

SRAM WRITE

A write cycle is performed whenever \bar{E} and \bar{W} are LOW. The address inputs must be stable prior to entering the WRITE cycle and must remain stable until either \bar{E} or \bar{W} go HIGH at the end of the cycle. The data on pins DQ_{0-7} will be written into the memory if it is valid t_{DVWH} before the end of a \bar{W} controlled WRITE or t_{DVEH} before the end of an \bar{E} controlled WRITE.

It is recommended that \bar{G} be kept HIGH during the entire WRITE cycle to avoid data bus contention on common I/O lines. If \bar{G} is left LOW, internal circuitry will turn off the output buffers t_{WLOZ} after \bar{W} goes LOW.

NONVOLATILE STORE

The STK11C68-M STORE cycle is initiated by executing sequential READ cycles from six specific address locations. By relying on READ cycles only, the STK11C68-M implements nonvolatile operation while remaining pin-for-pin compatible with standard 8Kx8 SRAMs. During the STORE cycle, an erase of the previous nonvolatile data is first performed, followed by a program of the nonvolatile elements. The program operation copies the SRAM data into nonvolatile elements. Once a STORE cycle is initiated, further input and output are disabled until the cycle is completed.

Because a sequence of reads from specific addresses is used for STORE initiation, it is important that no other read or write accesses intervene in the sequence or the sequence will be aborted and no STORE or

RECALL will take place.

To initiate the STORE cycle the following READ sequence must be performed:

- | | | | |
|----|--------------|------------|----------------------|
| 1. | Read address | 0000 (hex) | Valid READ |
| 2. | Read address | 1555 (hex) | Valid READ |
| 3. | Read address | 0AAA (hex) | Valid READ |
| 4. | Read address | 1FFF (hex) | Valid READ |
| 5. | Read address | 10F0 (hex) | Valid READ |
| 6. | Read address | 0F0F (hex) | Initiate STORE Cycle |

Once the sixth address in the sequence has been entered, the STORE cycle will commence and the chip will be disabled. It is important that READ cycles and not WRITE cycles be used in the sequence, although it is not necessary that \bar{G} be LOW for the sequence to be valid. After the t_{STORE} cycle time has been fulfilled, the SRAM will again be activated for READ and WRITE operation.

HARDWARE PROTECT

The STK11C68-M offers hardware protection against inadvertent STORE cycles through V_{CC} Sense. A STORE cycle will not be initiated, and one in progress will discontinue, if V_{CC} goes below 3.8V. 3.8V is a typical, characterized value.

NONVOLATILE RECALL

A RECALL cycle of the EEPROM data into the SRAM is initiated with a sequence of READ operations in a manner similar to the STORE initiation. To initiate the RECALL cycle the following sequence of READ operations must be performed:

- | | | | |
|----|--------------|------------|-----------------------|
| 1. | Read address | 0000 (hex) | Valid READ |
| 2. | Read address | 1555 (hex) | Valid READ |
| 3. | Read address | 0AAA (hex) | Valid READ |
| 4. | Read address | 1FFF (hex) | Valid READ |
| 5. | Read address | 10F0 (hex) | Valid READ |
| 6. | Read address | 0F0E (hex) | Initiate RECALL Cycle |

Internally, RECALL is a two step procedure. First, the SRAM data is cleared and second, the nonvolatile information is transferred into the SRAM cells. The RECALL operation in no way alters the data in the EEPROM cells. The nonvolatile data can be recalled an unlimited number of times.

On power-up, once V_{CC} exceeds the V_{CC} sense voltage of 3.8V, a RECALL cycle is automatically initiated. The voltage on the V_{CC} pin must not drop below 3.8V once it has risen above it in order for the RECALL to operate properly. Due to this automatic RECALL, SRAM operation cannot commence until t_{RECALL} after V_{CC} exceeds 3.8V. 3.8V is a typical, characterized value.

ORDERING INFORMATION

STK11C68 - 5 C 30 M

Temperature Range

M = Military (-55 to 125 degrees C)

Access Time

30 = 30ns

35 = 35ns

45 = 45ns

55 = 55ns

Package

C = Ceramic 28 pin 300-mil DIP

L = Ceramic 28 pin LCC

Retention / Endurance

blank = 10 years / 10,000 cycles

5 = 10 years / 100,000 cycles